



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

SOT-363 Plastic-Encapsulate DIODE

BAV99BRW

SWITCHING DIODE

SOT-363



FEATURES

Power dissipation

P_D : 200 mW ($T_{amb}=25^{\circ}C$)

Collector current

I_F : 150 mA

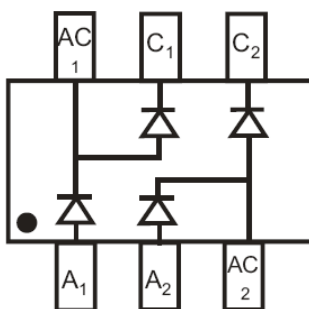
Collector-base voltage

V_R : 75 V

Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$

MARKING:KGJ



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)R}$	$I_R = 2.5\mu A$	75		V
Reverse voltage leakage current	I_R	$V_R = 75V$ $V_R = 20V$		2.5 0.025	μA
Forward voltage	V_F	$I_F = 1mA$ $I_F = 10mA$ $I_F = 50mA$ $I_F = 150mA$		715 855 1000 1250	mV
Junction capacitance	C_j	$V_R = 0V$ $f = 1MHz$		2	pF
Reveres recovery time	t_{rr}	$I_F = I_R = 10mA$ $I_{rr} = 0.1I_R$ $R_L = 100\Omega$		4	nS

Typical Characteristics

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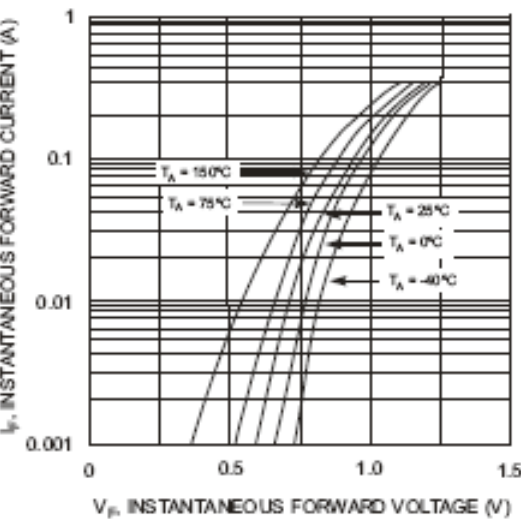


Fig. 1 Forward Characteristics

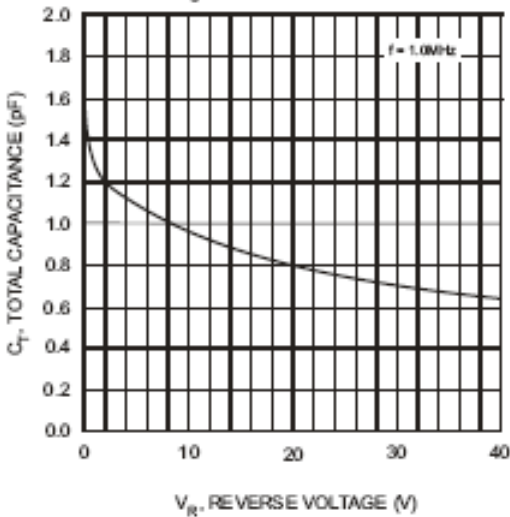


Fig. 3 Typical Capacitance vs. Reverse Voltage

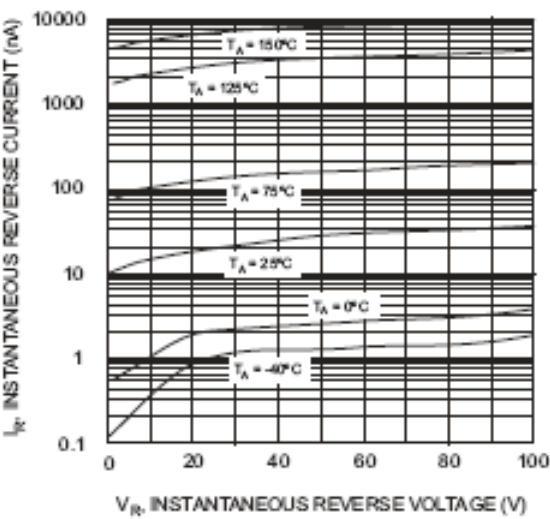


Fig. 2 Typical Reverse Characteristics

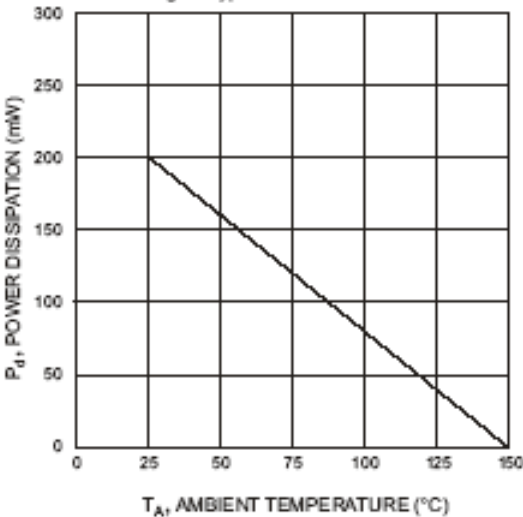


Fig. 4 Power Derating Curve